

#### NCE N-Channel Enhancement Mode Power MOSFET

#### **Description**

The NCE8290AC uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. This device is suitable for use in PWM, load switching and general purpose applications.

#### **General Features**

•  $V_{DS} = 82V, I_D = 90A$  $R_{DS(ON)} < 12 \text{ m}\Omega @ V_{GS} = 10V$  (Typ:9mΩ)

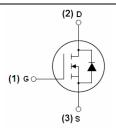
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Special designed for convertors and power controls
- Good stability and uniformity with high E<sub>AS</sub>
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

#### **Application**

- Power switching application
- Hard switched and High frequency circuits
- Uninterruptible power supply

100% UIS TESTED!

100% ΔVds TESTED!



#### Schematic diagram



#### Marking and pin assignment



TO-220-3L top view

#### **Package Marking and Ordering Information**

| Device Marking | Device    | Device Package | Reel Size | Tape width | Quantity |
|----------------|-----------|----------------|-----------|------------|----------|
| NCE8290AC      | NCE8290AC | TO-220-3L      | -         | -          | -        |

## Absolute Maximum Ratings (T<sub>A</sub>=25 ℃ unless otherwise noted)

| Parameter  | Symbol                | Limit      | Unit          |
|--|-----------------------|------------|---------------|
| Drain-Source Voltage                             | V <sub>DS</sub>       | 82         | V             |
| Gate-Source Voltage                              | V <sub>G</sub> s      | ±20        | V             |
| Drain Current-Continuous                         | I <sub>D</sub>        | 90         | A             |
| Drain Current-Continuous(T <sub>C</sub> =100°C)  | I <sub>D</sub> (100℃) | 63.6       | Α             |
| Pulsed Drain Current                             | I <sub>DM</sub>       | 320        | Α             |
| Maximum Power Dissipation                        | P <sub>D</sub>        | 130        | W             |
| Derating factor                                  |                       | 0.87       | W/℃           |
| Single pulse avalanche energy (Note 5)           | E <sub>AS</sub>       | 380        | mJ            |
| Operating Junction and Storage Temperature Range | $T_J, T_{STG}$        | -55 To 175 | ${\mathbb C}$ |

# NCE8290AC

#### **Thermal Characteristic**

### Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

| Parameter                          | Symbol              | Condition                                 | Min | Тур      | Max  | Unit |
|------------------------------------|---------------------|---|-----|----------|------|------|
| Off Characteristics                |                     |   |     |          |      |      |
| Drain-Source Breakdown Voltage     | BV <sub>DSS</sub>   | V <sub>GS</sub> =0V I <sub>D</sub> =250µA | 82  | -        | -    | V    |
| Zero Gate Voltage Drain Current    | I <sub>DSS</sub>    | V <sub>DS</sub> =82V,V <sub>GS</sub> =0V  | -   | -        | 1    | μΑ   |
| Gate-Body Leakage Current          | I <sub>GSS</sub>    | V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V | -   | -        | ±100 | nA   |
| On Characteristics (Note 3)        |                     |   |     |          |      |      |
| Gate Threshold Voltage             | V <sub>GS(th)</sub> | $V_{DS}=V_{GS}$ , $I_{D}=250\mu A$        | 2   | 3        | 4    | V    |
| Drain-Source On-State Resistance   | R <sub>DS(ON)</sub> | V <sub>GS</sub> =10V, I <sub>D</sub> =20A | -   | 9        | 12   | mΩ   |
| Forward Transconductance           | <b>g</b> FS         | V <sub>DS</sub> =5V,I <sub>D</sub> =20A   | -   | 30       | -    | S    |
| Dynamic Characteristics (Note4)    |                     |   |     |          |      |      |
| Input Capacitance                  | C <sub>lss</sub>    | )/ OF)/// O)/                             | -   | 4414     | -    | PF   |
| Output Capacitance                 | C <sub>oss</sub>    | V <sub>DS</sub> =25V,V <sub>GS</sub> =0V, | -   | 219      | -    | PF   |
| Reverse Transfer Capacitance       | C <sub>rss</sub>    | F=1.0MHz                                  | -   | 188      | -    | PF   |
| Switching Characteristics (Note 4) | ,                   |   | •   | <u>I</u> |      |      |
| Turn-on Delay Time                 | $t_{d(on)}$         |   | -   | 19       | -    | nS   |
| Turn-on Rise Time                  | t <sub>r</sub>      | $V_{DD}$ =40 $V$ , $R_L$ =15 $\Omega$     | -   | 12       | -    | nS   |
| Turn-Off Delay Time                | t <sub>d(off)</sub> | $R_G$ =2.5 $\Omega$ , $V_{GS}$ =10 $V$    | -   | 40       | -    | nS   |
| Turn-Off Fall Time                 | t <sub>f</sub>      |   | -   | 15       | -    | nS   |
| Total Gate Charge                  | Qg                  | \/ 40\/ L 00 A                            | -   | 81.5     | -    | nC   |
| Gate-Source Charge                 | Q <sub>gs</sub>     | $V_{DS}=40V, I_{D}=20A,$                  | -   | 26.9     | -    | nC   |
| Gate-Drain Charge                  | $Q_{gd}$            | V <sub>GS</sub> =10V                      | -   | 23.7     | -    | nC   |
| Drain-Source Diode Characteristics |                     |   | •   |          |      |      |
| Diode Forward Voltage (Note 3)     | V <sub>SD</sub>     | V <sub>GS</sub> =0V,I <sub>S</sub> =20A   | -   | -        | 1.2  | V    |
| Diode Forward Current (Note 2)     | Is                  |   | -   | -        | 90   | Α    |
| Reverse Recovery Time              | t <sub>rr</sub>     | Tj=25°C,I <sub>F</sub> =20A               | -   | 36       | -    | nS   |
| Reverse Recovery Charge            | Qrr                 | di/dt=100A/µs (Note3)                     | -   | 54       | -    | nC   |

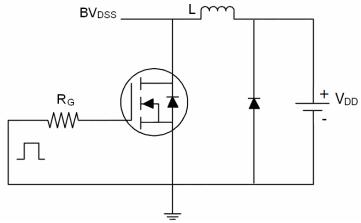
#### Notes:

- $\textbf{1.} \ \textbf{Repetitive Rating: Pulse width limited by maximum junction temperature.}$
- **2.** Surface Mounted on FR4 Board,  $t \le 10$  sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- **5.** EAS condition: Tj=25  $^{\circ}\text{C}$  ,VDD=40V,VG=10V,L=0.5mH,Rg=25 $\Omega$

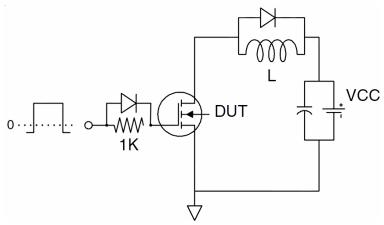


# **Test Circuit**

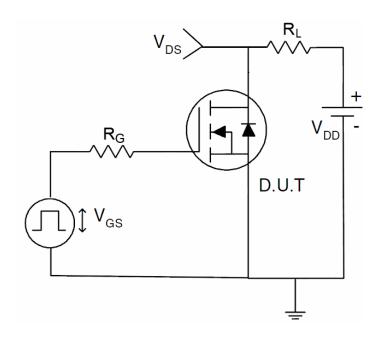
## 1) E<sub>AS</sub> Test Circuits



### 2) Gate Charge Test Circuit

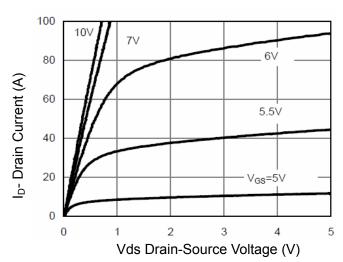


### 3) Switch Time Test Circuit

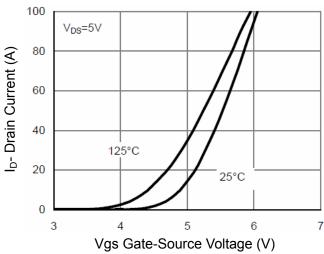




## Typical Electrical and Thermal Characteristics (Curves



**Figure 1 Output Characteristics** 



**Figure 2 Transfer Characteristics** 

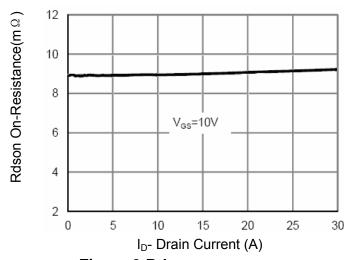
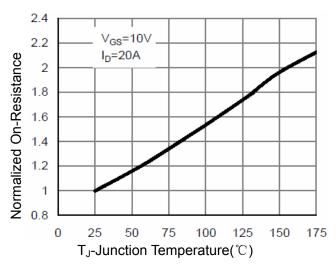


Figure 3 Rdson- Drain Current



**Figure 4 Rdson-Junction Temperature** 

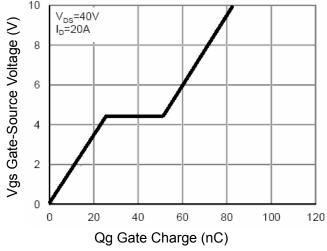


Figure 5 Gate Charge

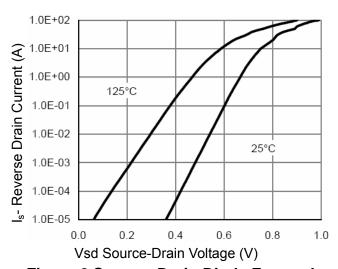


Figure 6 Source- Drain Diode Forward



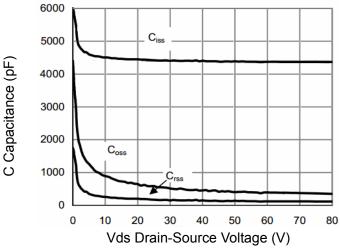


Figure 7 Capacitance vs Vds

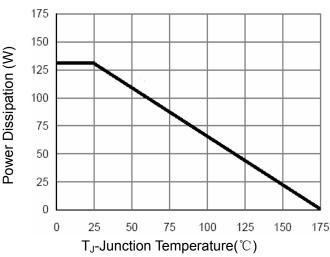
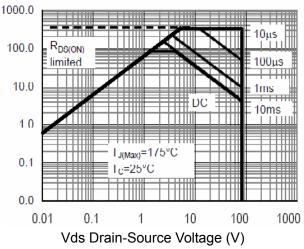


Figure 9 Power De-rating



**Figure 8 Safe Operation Area** 

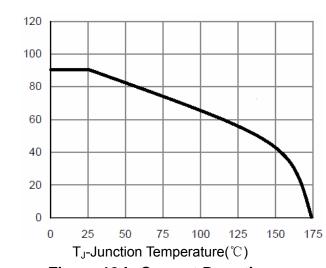
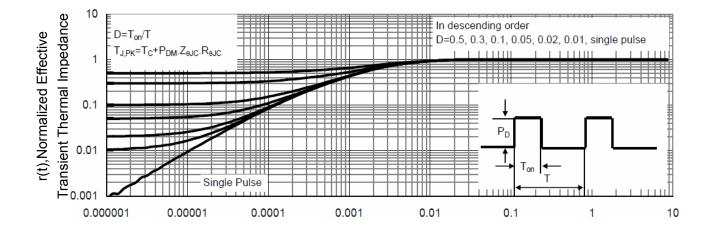


Figure 10 I<sub>D</sub> Current De-rating



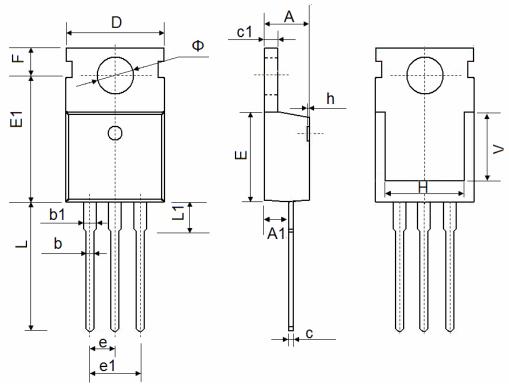
D- Drain Current (A)

Square Wave Pluse Duration(sec)

Figure 11 Normalized Maximum Transient Thermal Impedance



## **TO-220-3L Package Information**



| Compleal | Dimensions | In Millimeters | Dimensions In Inches |       |  |
|----------|------------|----------------|----------------------|-------|--|
| Symbol   | Min.       | Max.           | Min.                 | Max.  |  |
| Α        | 4.400      | 4.600          | 0.173                | 0.181 |  |
| A1       | 2.250      | 2.550          | 0.089                | 0.100 |  |
| b        | 0.710      | 0.910          | 0.028                | 0.036 |  |
| b1       | 1.170      | 1.370          | 0.046                | 0.054 |  |
| С        | 0.330      | 0.650          | 0.013                | 0.026 |  |
| c1       | 1.200      | 1.400          | 0.047                | 0.055 |  |
| D        | 9.910      | 10.250         | 0.390                | 0.404 |  |
| E        | 8.9500     | 9.750          | 0.352                | 0.384 |  |
| E1       | 12.650     | 12.950         | 0.498                | 0.510 |  |
| е        | 2.540 TYP. |                | 0.100 TYP.           |       |  |
| e1       | 4.980      | 5.180          | 0.196                | 0.204 |  |
| F        | 2.650      | 2.950          | 0.104                | 0.116 |  |
| Н        | 7.900      | 8.100          | 0.311                | 0.319 |  |
| h        | 0.000      | 0.300          | 0.000                | 0.012 |  |
| L        | 12.900     | 13.400         | 0.508                | 0.528 |  |
| L1       | 2.850      | 3.250          | 0.112                | 0.128 |  |
| V        | 7.500 REF. |                | 0.295 REF.           |       |  |
| Ф        | 3.400      | 3.800          | 0.134                | 0.150 |  |



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